

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Application Number	10/524,809
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2895
Examiner Name	Fernando L. Toledo
Attorney Docket Number	070050.2721

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
	1.	4514895	5/7/1985	Nishimura, Tadashi
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	5.	5436095	7/25/1995	Mizuno, Fumio ; Moriuchi, Noboru ; Shirai, Seiichiro ; Morita, Masayuki
	6.	5466908	11/14/1995	Hosoya, Kimio ; Teruya, Yoshihiro ; Kobayashi, Yasushi
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	10.	5616506	4/1/1997	Takemura, Yasuhiko
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	14.	6093934	7/25/2000	Yamazaki, Shunpei ; Teramoto, Satoshi ; Koyama, Jun ; Ogata, Yasushi ; Hayakawa, Masahiko ; Osame, Mitsuaki ; Ohtani, Hisashi ; Hamatani, Toshiji
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	23.	6358784	3/19/2002	Zhang, Hongyong ; Yamazaki, Shunpei ; Takemura, Yasuhiko
	24.	6388386	5/14/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio

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	27.	6410373	6/25/2002	Chang, Ting Chang ; Zan, Hsiao Wen ; Shih, Po Sheng
	28.	6429100	8/6/2002	Yoneda, Kiyoshi
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	63.	7091411	8/15/2006	Falk, Fritz ; Andrae, Gudrun

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	81.	20030148565	8/7/2003	Yamanaka, Hideo
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	85.	20040169176	9/2/2004	Peterson, Paul, E. ; Stasiak, James
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	87.	20040222187	11/11/2004	Lin, Kun Chih
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